## Development of p-channel CCDs for NeXT

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(Abstract) We develop an X-ray CCD camera system (SXI: Soft X-ray Imager) as a focal plane detector of an X-ray telescope onboard NeXT, the next Japanese X-ray astronomical satellite mission. We develop p-channel CCDs as the goal of SXI. We report the test results of two p-channel CCD devices, Pch-15 and Pch-teg. Pch-15 is a front illuminated CCD consisting of 512 x 512 pixels with a pixel size of 24 µm x 24 µm. Pch-15 was fabricated on an n-type silicon wafer of 600 µm thickness. The thickness of depletion layer of Pch-15 was evaluated to be 290±33 µm from the detection efficiency of 22.4 and 24.9 keV emission lines from <sup>109</sup>Cd. Pch-teg consists of 328 x 320 pixels with a pixel size of 14.5 µm x 15 µm. Pch-teg was designed as a fully depleted front illuminated CCD with wafer thickness of 200 µm. The thickness of depletion layer of Pch-teg was evaluated to be 172±13 µm. We detected the coxygen K line at 527 eV with Pch-teg and evaluated the energy resolution, readout noise, and charge transfer inefficiency for both the devices by <sup>65</sup>Fe irradiation.

## **1. SXI: Soft X-ray Imager**

 The SXI is an X-ray CCD camera system

 onboard NeXT, the next Japanese X-ray

 astronomical satellite mission. The SXI is

 required to cover X-ray energy range in the

 0.5-12 keV.

 Energy band
 0.5 - 12 keV

 Pixel size
 24 µm× 24 µm

Requirements f	for SXI	
СТІ	< 5 × 10 <sup>-6</sup>	
Readout noise	< 5 e <sup></sup>	
Energy resolution	< 135 eV at 5.9keV	1400 1300 Connector
Readout node	8	
FOV	19 '×19 '	Elevible print
Image area	50 mm×50 mm	+ 550 +
Storage array	$2048 \times 2048$	CCD assembly
Image array	$2048\times2048$	

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## 2. P-channel CCD

l	Baseline	N-type (P
Wafer l	P-type (N channel)	<u>channel</u> )
Depletion layer 7	70~100 μm	200 µm
Illumination method l	Front illuminated	Back illuminated

We develop p-channel CCDs as the goal of the SXI. Although n-channel CCDs have been employed for previous X-ray astronomical satellites, we set p-channel CCDs as the goal of the SXI because p-channel CCDs could have thicker depletion layer than n-channel CCDs.

$d \sim (\mu \rho V)^{0.5} \qquad \begin{array}{c} \mu \text{ mobility of major } \alpha \\ \rho \text{ resistivity of wafe} \end{array}$	r carrier afer
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The mobility of the electron ,the major carrier of n-type silicon wafer for pchannel CCD, is three times larger than that of the hole, the major carrier of p-type silicon wafer for n-channel CCD. Besides, it is easy to obtain n-type silicon wafer with high and uniform resistivity compared to p-type silicon wafer.



## 4. Test device Pch-teg 4.1 Specification Specification Pixel size 14.5 μm x 15 μm 328 x 320 200 μm Format Wafer thickness Schematic of cross section Illuminated method FI (Front illuminated) electrod Performance Energy resolution 143±3 eV at 5.9 keV Readout noise CTI (horizontal) 7 electrons < 10<sup>-5</sup> CTI (Vertical) Depletion layer < 10<sup>-5</sup> 172±13 μπ 4.2 <sup>55</sup>Fe irradiation -70°C Operation temp Readout speed 60 kHz Mn kα 5.9 keV Mn kβ 6.5 keV Counts 10 1 X-ray events t [ADU] X-ray histogram of 55Fe obtained with Pch-15. limage of X-ray events with a pixel The energy resolution was 143±3 eV of FWHM, size of 14.5µm×15µm and the readout noise was 7 electrons (r.m.s). 4.3 Low energy responsivity



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